Client's ref.: 91178

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Our ref: 0548-9210us/final/yyhsu/Kevin

ABSTRACT OF THE DISCLOSURE

A method of forming bit line contact. A substrate has device and peripheral contact areas, with the device area having transistors including a gate electrode, a doped region, and a pair of barrier spacers formed on opposing sidewalls of two adjacent gate electrodes. A dielectric layer is formed overlying the substrate, and a contact formed through the dielectric layer, exposing the doped region. Finally, a conductive layer is formed as a bit line contact plug to fill the bit line contact.